74HC573; 74HCT573

Octal D-type transparent latch; 3-state

Rev. 7 — 4 March 2016

Product data sheet

1. **General description**

The 74HC573; 74HCT573 is an 8-bit D-type transparent latch with 3-state outputs. The device features latch enable (LE) and output enable (OE) inputs. When LE is HIGH, data at the inputs enter the latches. In this condition the latches are transparent, a latch output will change each time its corresponding D-input changes. When LE is LOW the latches store the information that was present at the inputs a set-up time preceding the HIGH-to-LOW transition of LE. A HIGH on OE causes the outputs to assume a high-impedance OFF-state. Operation of the OE input does not affect the state of the latches. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. **Features and benefits**

- Input levels:
 - ◆ For 74HC573: CMOS level
 - ◆ For 74HCT573: TTL level
- Inputs and outputs on opposite sides of package allowing easy interface with microprocessors
- Useful as input or output port for microprocessors and microcomputers
- 3-state non-inverting outputs for bus-oriented applications
- Common 3-state output enable input
- Multiple package options
- Complies with JEDEC standard no. 7 A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2 000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

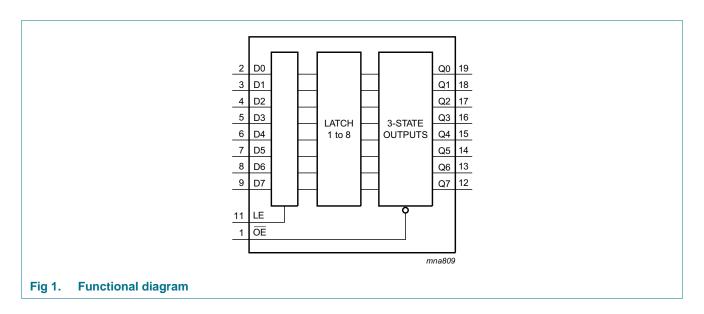


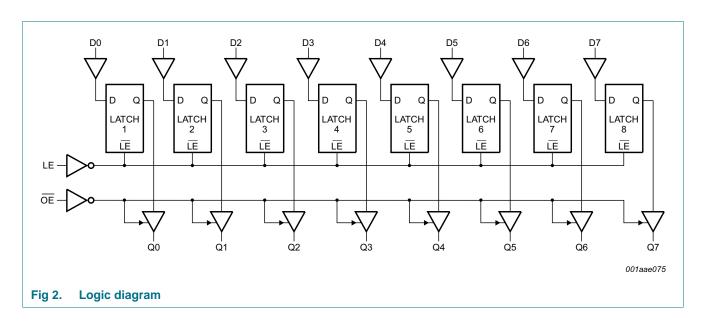
3. Ordering information

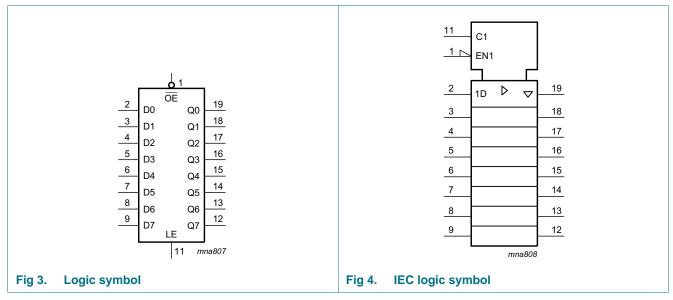
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC573D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads;	SOT163-1
74HCT573D			body width 7.5 mm	
74HC573DB	−40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads;	SOT339-1
74HCT573DB			body width 5.3 mm	
74HC573PW	–40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads;	SOT360-1
74HCT573PW			body width 4.4 mm	
74HC573BQ	–40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very	SOT764-1
74HCT573BQ			thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm	

4. Functional diagram

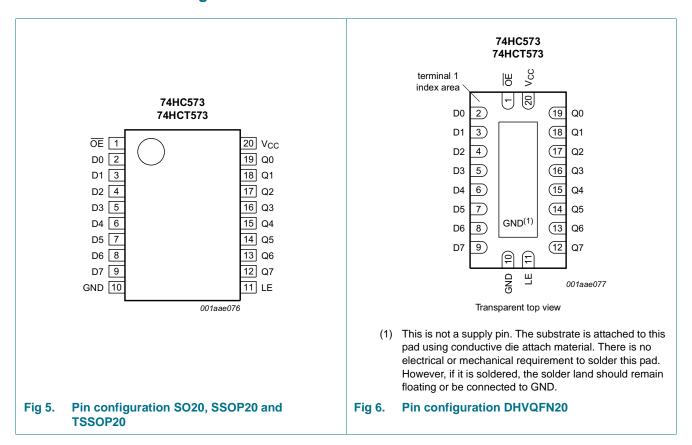






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
ŌĒ	1	3-state output enable input (active LOW)
D[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
LE	11	latch enable input (active HIGH)
Q[0:7]	19, 18, 17, 16, 15, 14, 13, 12	3-state latch output
Vcc	20	supply voltage

6. Functional description

Table 3. Function table[1]

Operating mode	Control		Input	Internal	Output							
	OE	LE	Dn	latches	Qn							
Enable and read register (transparent	L	Н	L	L	L							
mode)			Н	Н	Н							
Latch and read register	L	L	I	L	L							
			h	Н	Н							
Latch register and disable outputs	Н	L	L	L	L	L	L	L	L	1	L	Z
			h	Н	Z							

^[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the HIGH-to-LOW LE transition;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_{I} < -0.5 \text{ V or } V_{I} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
I _{OK}	output clamping current	$V_{O} < -0.5 \text{ V or } V_{O} > V_{CC} + 0.5 \text{ V}$	-	±20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-	±35	mA
I _{CC}	supply current		-	+70	mA
I _{GND}	ground current		-70	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	SO20, SSOP20, TSSOP20 and DHVQFN20 [1] packages	-	500	mW

^[1] For SO20: P_{tot} derates linearly with 8 mW/K above 70 °C.

For SSOP20 and TSSOP20 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

For DHVQFN20 package: P_{tot} derates linearly with 4.5 mW/K above 60 $^{\circ}\text{C}.$

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the HIGH-to-LOW LE transition;

Z = high-impedance OFF-state.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions 74HC573				7	3	Unit	
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC573	3									
V _{IH} HIGH-level		V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -20 \mu A; V_{CC} = 6.0 V$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 6.0$ V; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10.0	μА

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C t	o +85 °C	-40 °C t	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-					pF
74HCT5	73									
V_{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -6 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_{O} = 6.0 \text{ mA}$	-	0.16	0.26	-	0.33	-	0.4	V
I ₁	input leakage current	$V_1 = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND	-	-	±0.5	-	±5.0	-	±10	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	$\begin{aligned} &V_{I} = V_{CC} - 2.1 \text{ V;} \\ &\text{other inputs at } V_{CC} \text{ or GND;} \\ &V_{CC} = 4.5 \text{ V to } 5.5 \text{ V;} \\ &I_{O} = 0 \text{ A} \end{aligned}$								
		per input pin; Dn inputs	-	35	126	-	158	-	172	μΑ
		per input pin; LE input	-	65	234	-	293	-	319	μΑ
		per input pin; OE input	-	125	450	-	563	-	613	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see Figure 11.

Symbol	Parameter	Conditions			25 °C		-40 °C 1	to +85 °C	-40 °C t	o +125 °C	Unit
			ı	Min	Тур	Max	Min	Max	Min	Max	
74HC573	3										-
t _{pd}	propagation	Dn to Qn; see Figure 7	<u>[1]</u>								
	delay	V _{CC} = 2.0 V		-	47	150	-	190	-	225	ns
		V _{CC} = 4.5 V		-	17	30	-	38	-	45	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V		-	14	26	-	33	-	38	ns
t _{pd}	propagation	LE to Qn; see Figure 8	[1]								
	delay	V _{CC} = 2.0 V		-	50	150	-	190	-	225	ns
		V _{CC} = 4.5 V		-	18	30	-	38	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF		-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V		-	14	26	-	33	-	38	ns
t _{en}	enable time	OE to Qn; see Figure 9	[2]								
		V _{CC} = 2.0 V		-	44	140	-	175	-	210	ns
		V _{CC} = 4.5 V		-	16	28	-	35	-	42	ns
		V _{CC} = 6.0 V		-	13	24	-	30	-	36	ns
t _{dis}	disable time		[3]								
		V _{CC} = 2.0 V		-	55	150	-	190	-	225	ns
		V _{CC} = 4.5 V		-	20	30	-	38	-	45	ns
		V _{CC} = 6.0 V		-	16	26	-	33	-	38	ns
t _t	transition	Qn; see Figure 7	[4]								
	time	V _{CC} = 2.0 V		-	14	60	-	75	-	90	ns
		V _{CC} = 4.5 V		-	5	12	-	15	-	18	ns
		V _{CC} = 6.0 V		-	4	10	-	13	-	15	ns
t _W	pulse width	LE HIGH; see Figure 8									
		V _{CC} = 2.0 V		80	14	-	100	-	120	-	ns
		V _{CC} = 4.5 V		16	5	-	20	-	24	-	ns
		V _{CC} = 6.0 V		14	4	-	17	-	20	-	ns
t _{su}	set-up time	Dn to LE; see Figure 10									
	-	V _{CC} = 2.0 V		50	11	-	65	-	75	-	ns
		V _{CC} = 4.5 V		10	4	-	13	-	15	-	ns
		V _{CC} = 6.0 V		9	3	-	11	-	13	-	ns
t _h	hold time	Dn to LE; see Figure 10									+
		V _{CC} = 2.0 V		5	3	-	5	-	5	-	ns
		V _{CC} = 4.5 V		5	1	-	5	-	5	-	ns
		V _{CC} = 6.0 V		5	1	-	5	-	5	-	ns
C _{PD}	power dissipation capacitance		[5]	-	26	-	-	-	-	-	pF

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50 \text{ pF}$ unless otherwise specified; for test circuit see <u>Figure 11</u>.

Symbol	Parameter	Conditions			25 °C		-40 °C	to +85 °C	-40 °C t	o +125 °C	Unit
				Min	Тур	Max	Min	Max	Min	Max	
74HCT5	73							1			-1
t _{pd}	propagation	Dn to Qn; see Figure 7	[1]								
	delay	V _{CC} = 4.5 V		-	20	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF		-	17	-	-	-	-	-	ns
t _{pd}	propagation	LE to Qn; see Figure 8	[1]								
	delay	V _{CC} = 4.5 V		-	18	35	-	44	-	53	ns
		$V_{CC} = 5 \text{ V}; C_L = 15 \text{ pF}$		-	15	-	-	-	-	-	ns
t _{en}	enable time	OE to Qn; see Figure 9	[2]								
		V _{CC} = 4.5 V		-	17	30	-	38	-	45	ns
t _{dis}	disable time	OE to Qn; see Figure 9	[3]								
		V _{CC} = 4.5 V		-	18	30	-	38	-	45	ns
t _t	transition	Qn; see Figure 7	[4]								
	time	V _{CC} = 4.5 V		-	5	12	-	15	-	18	ns
t _W	pulse width	LE HIGH; see Figure 8									
		V _{CC} = 4.5 V		16	5	-	20	-	24	-	ns
t _{su}	set-up time	Dn to LE; see Figure 10									
		V _{CC} = 4.5 V		13	7	-	16	-	20	-	ns
t _h	hold time	Dn to LE; see Figure 10									
		V _{CC} = 4.5 V		9	4	-	11	-	15	-	ns
C _{PD}	power dissipation capacitance	C_L = 50 pF; f = 1 MHz; V _I = GND to V _{CC} - 1.5 V	[5]	-	26	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .
- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

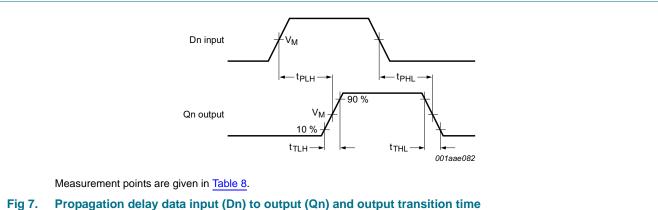
C_L = output load capacitance in pF;

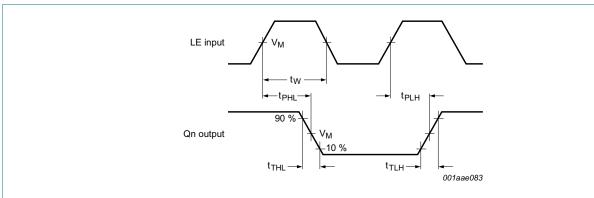
 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

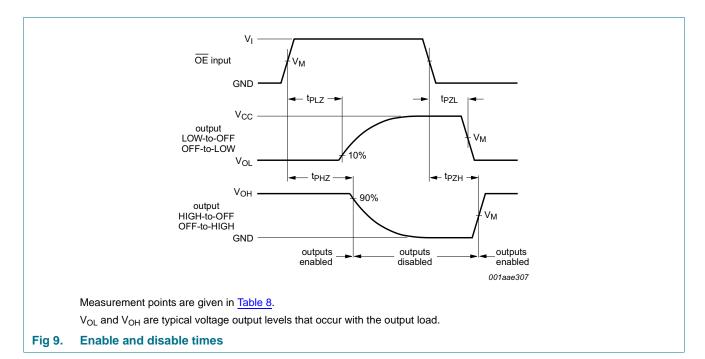
11. Waveforms





Measurement points are given in Table 8.

Fig 8. Pulse width latch enable input (LE), propagation delay latch enable input (LE) to output (Qn) and output transition time



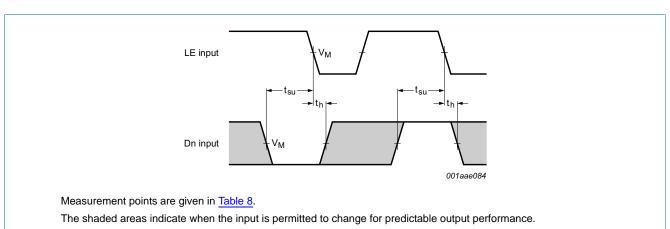
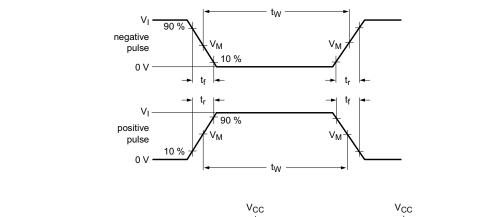
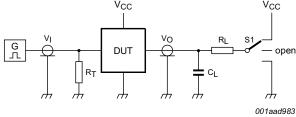


Fig 10. Set-up and hold times for data input (Dn) to latch input (LE)

Table 8. Measurement points

Туре	Input	Output
	V _M	V _M
74HC573	0.5V _{CC}	0.5V _{CC}
74HCT573	1.3 V	1.3 V





Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 C_L = Load capacitance including jig and probe capacitance.

R_L = Load resistance.

S1 = Test selection switch.

Fig 11. Test circuit for measuring switching times

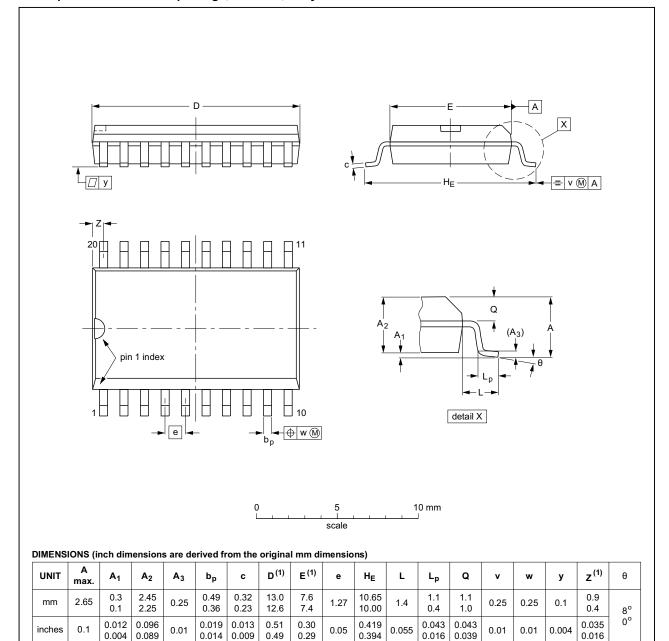
Table 9. Test data

Туре	Input		Load		S1 position			
	VI	t _r , t _f	C _L R _L t _P		t _{PHL} , t _{PLH}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}	
74HC573	V _{CC}	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	
74HCT573	3 V	6 ns	15 pF, 50 pF	1 kΩ	open	GND	V _{CC}	

12. Package outline

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT163-1	075E04	MS-013				99-12-27 03-02-19	

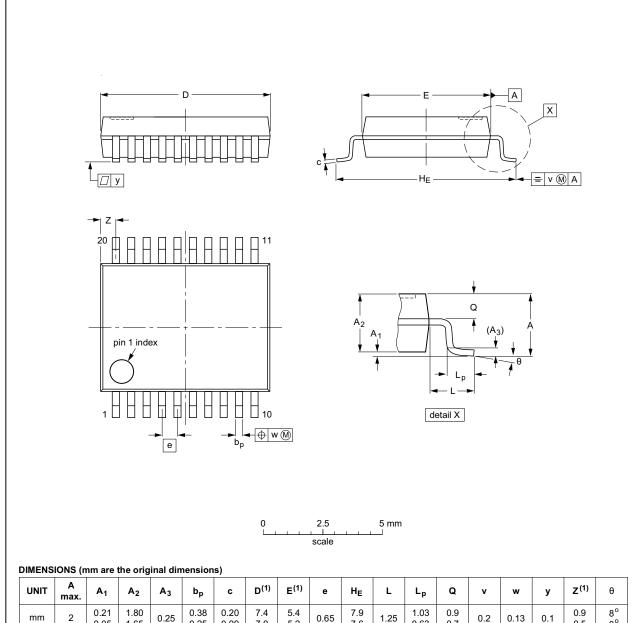
Fig 12. Package outline SOT163-1 (SO20)

74HC_HCT573

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SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	ø	v	¥	у	Z ⁽¹⁾	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	7.4 7.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	0.9 0.5	8° 0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

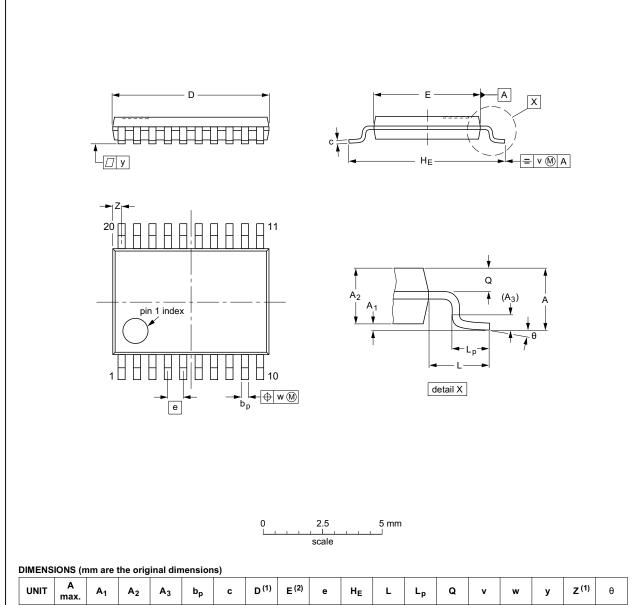
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT339-1		MO-150				99-12-27 03-02-19	

Fig 13. Package outline SOT339-1 (SSOP20)

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TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



UN	IT A max.	A ₁	A ₂	A ₃	bp	С	D (1)	E (2)	е	HE	L	Lp	Q	v	w	у	Z (1)	θ
mr	m 1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

	REFER	EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	MO-153				99-12-27 03-02-19
	IEC	IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

Fig 14. Package outline SOT360-1 (TSSOP20)

74HC_HCT573

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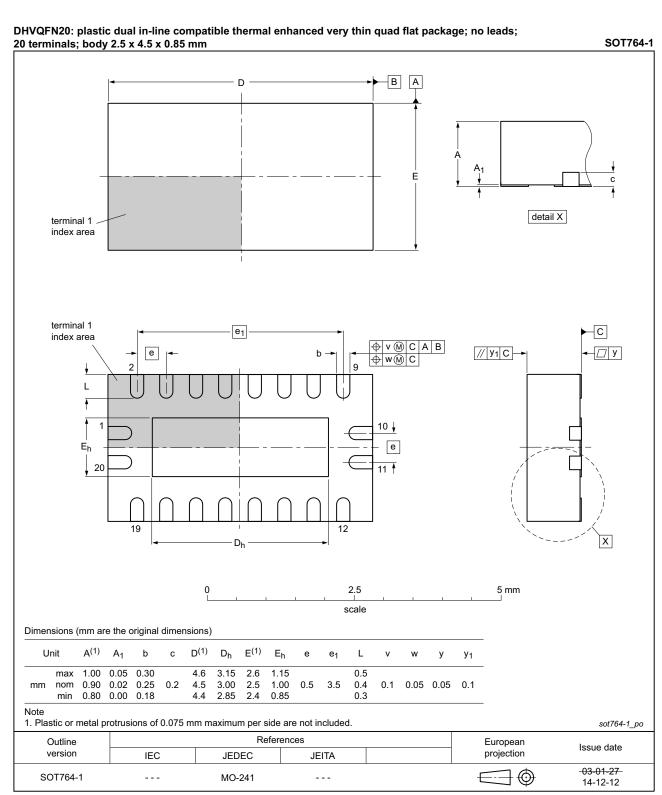


Fig 15. Package outline SOT764-1 (DHVQFN20)

74HC_HCT573

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
74HC_HCT573 v.7	20160304	Product data sheet	-	74HC_HCT573 v.6				
Modifications:	Type number	ers 74HC573N and 74HCT	573N (SOT146-1) re	moved.				
74HC_HCT573 v.6	20150126	Product data sheet	-	74HC_HCT573 v.5				
Modifications:	• <u>Table 7</u> : Pov	wer dissipation capacitanc	e condition for 74HC	Γ573 is corrected.				
74HC_HCT573 v.5	20120815	Product data sheet	-	74HC_HCT573 v.4				
Modifications:	Alternative of	descriptive title corrected (errata).					
74HC_HCT573 v.4	20120806	Product data sheet	-	74HC_HCT573 v.3				
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. Legal texts have been adapted to the new company name where appropriate. 							
74HC_HCT573 v.3	20060117	Product data sheet	-	74HC_HCT573_CNV v.2				
74HC_HCT573_CNV v.2	19901201	Product specification	-	-				

15. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Octal D-type transparent latch; 3-state

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